



Application No. 10/529,373

Reply to Office Action

AMENDMENTS TO THE TITLE

Replace the title with:

Method of Fabricating ~~Thin-film Semiconductor~~ a Polycrystalline Film by
Crystallizing an Amorphous Film with Laser Light

AMENDMENTS TO THE SPECIFICATION

Delete the heading at page 5, line 12:

~~Description of the Reference Characters~~

Delete the paragraph at page 5, line 13:

~~1: pulse laser light source, 2: first pulse laser light, 8: focusing and irradiation optical system, 9: object to be irradiated, 12: bend mirror, 13: beam adjusting optical system, 14: stage, 21: focusing lens, 22: first pulse laser light (focused into a line), 24: profile (of focused first pulse laser light), 26: melted portion, 27: longitudinal direction (of a beam focused into a line), 29: crystal grain, 30: width direction (of a beam focused into a line), 31: lateral crystal growth, 32: arrow (showing a direction in which crystals grow), 33: region irradiated (by the first pulse laser light), 34: arrow (showing a direction in which the region irradiated by the first pulse laser light relatively scans), 35: arrow (showing the direction in which the substrate moves), 36: region (made into a polycrystalline silicon film by irradiation of the first pulse laser light), 37: crystal grain (produced in an end), 38, 41: region irradiated (by the second pulse laser light), 39: region (scanned by the region irradiated by the first pulse laser light as a next line), 40: arrow (showing the direction in which the region irradiated by the second pulse laser light scans), 201: insulation substrate, 202: base film, 203: amorphous silicon film, 204: arrow (showing the direction of laser irradiation), 206: (patterned) polycrystalline silicon film, 207: gate insulating film, 208: gate electrode, 209: source electrode, 210: drain electrode, 211: interlayer insulation film~~